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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/624,712	07/22/2003	Ralf van Bentum	2000.106700	3646
23720	7590	05/26/2005	EXAMINER	
WILLIAMS, MORGAN & AMERSON, P.C. 10333 RICHMOND, SUITE 1100 HOUSTON, TX 77042			VINH, LAN	
			ART UNIT	PAPER NUMBER
			1765	
DATE MAILED: 05/26/2005				

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No. 10/624,712	Applicant(s) BENTUM ET AL.	
	Examiner Lan Vinh	Art Unit 1765	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 09 May 2005.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-24 is/are pending in the application.
- 4a) Of the above claim(s) 18-24 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1,2,6-12 and 15-17 is/are rejected.
- 7) ☒ Claim(s) 3-5, 13 and 14 is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|---|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date <u>050604</u> . | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Election/Restrictions

1. Applicant's election of Group I, claims 1-17 in the reply filed on 5/9/2005 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 1-2, 6-10, 15 are rejected under 35 U.S.C. 102(b) as being anticipated by Choi et al (US 5,629,238)

Choi discloses a method for forming conductive line of semiconductor device. The method comprises the steps:

forming an narrow/isolation trench and a wide/contact trench in a substrate, wherein a width of said isolation trench is less than a width of said contact trench (fig. 7D)

depositing an insulating material 22 over the narrow/ isolation trench and said contact trench to substantially fill said isolation trench and reduce an effective width of said contact trench (col 4, lines 47-48; fig. 6A)

removing at least partially said insulating material from a bottom of said contact

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trench (col 5, lines 3-5)

filling in a conductive material into said contact trench to form a contact (col 4, lines 65-67; fig. 6C)

Regarding claim 2, Choi further discloses forming a buried conductive region 26 in said substrate below said contact trench such that said buried region at least partially overlaps with said contact trench, said buried conductive region being conductively coupled to said contact (col 5, lines 51-53)

Regarding claim 6, Choi discloses that the contact trench having a width and the insulating layer is formed by CVD (col 4, lines 1-5; fig. 5A)

Regarding claim 7, Choi discloses the step of anisotropically etching the insulating layer 40 (col 4, lines 48-49)

Regarding claim 8, Choi discloses the step of forming a etch stop layer 22 and depositing a dielectric layer 24 on layer 22 (col 5, lines 15-17)

Regarding claims 9-10, Choi discloses the step of filling the contact trench with conductive material such as tungsten and removing excess material by CMP (col 5, lines 35-41)

Regarding claim 15, Choi discloses forming the buried region 26 after forming the trenches (col 5, lines 50-55; fig. 7C)

Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

5. Claims 11-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Choi et al (US 5,629,238) in view of Lou et al (US 5,872,045)

Choi method has been described above. Unlike the instant claimed inventions as per claims 11-12, Choi fails to disclose using doped polysilicon as conductive material and forming a barrier layer on inner sidewalls of the contact trench

Lou discloses a method for fabricating STI comprises the steps of using doped polysilicon as conductive material and forming a barrier layer on inner sidewalls of the contact trench (col 5, lines 5-14)

Hence, one skilled in the art at the time the invention was made would have found it obvious to modify Choi method by using doped polysilicon as conductive material and forming a barrier layer on inner sidewalls of the contact trench as per Lou because Lou discloses that the doped polysilicon improves the removal rate uniformity across the substrate (see abstract) and the layer on inner sidewall of the trench serve as an oxidation barrier layer (col 5, lines 6-7)

6. Claims 16-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Choi et al (US 5,629,238) in view of Brown et al (US 6,498,372)

Choi method has been described above. Unlike the instant claimed inventions as per claims 16-17, Choi fails to disclose the step of implanting the substrate below the

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contact trench through the insulating layer to form the buried region after removing the insulating layer at the bottom of the contact trench

Brown discloses a method for forming electrical structure in semiconductor device comprises the step of implanting the substrate below the contact trench through the insulating layer to form the buried region after removing the insulating layer at the bottom of the contact trench (col 4, lines 15-20; fig. 3)

Hence, one skilled in the art at the time the invention was made would have found it obvious to modify Choi method by implanting the substrate below the contact trench through the insulating layer to form the buried region as per Brown because Brown discloses that it is known on the art to implant dopants through the trench into the substrate to form the doped buried region (col 4, lines 9-16)

Allowable Subject Matter

7. Claims 3-5, 13-14 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: Regarding claim 3, the cited prior art of record, taken alone or in combination, fails to disclose a method comprises the step of forming the buried conductive region prior to the formation of the isolation trench and contact trench, in combination with the rest of the limitation of claim 3. The closest cited prior art of Choi et al (US 5,629,238)

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discloses forming buried region 26 below contact trench after the formation of the isolation trench and contact trench (fig. 7B)

Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



LV
May 23, 2005